

## Electronic supplementary information

### High and Stable Photoelectrochemical Activity of ZnO/ZnSe/CdSe/Cu<sub>x</sub>S Core-Shell Nanowire Arrays: Nanoporous Surface with Cu<sub>x</sub>S as a Hole Mediator

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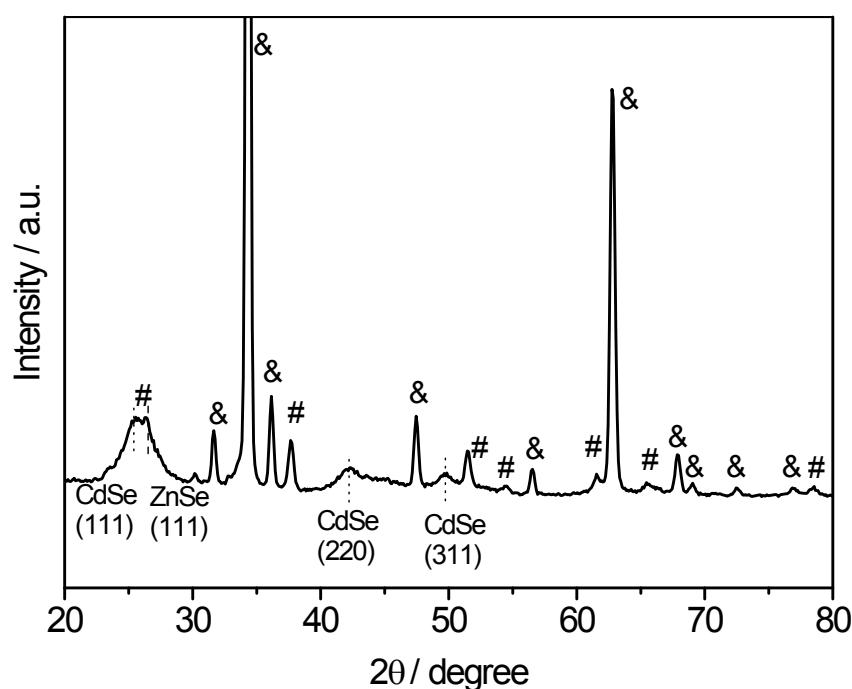


Figure S1. XRD pattern of ZnO/ZnSe/CdSe/Cu<sub>x</sub>S sample. Peaks from FTO and ZnO are indicated by # and &, respectively.

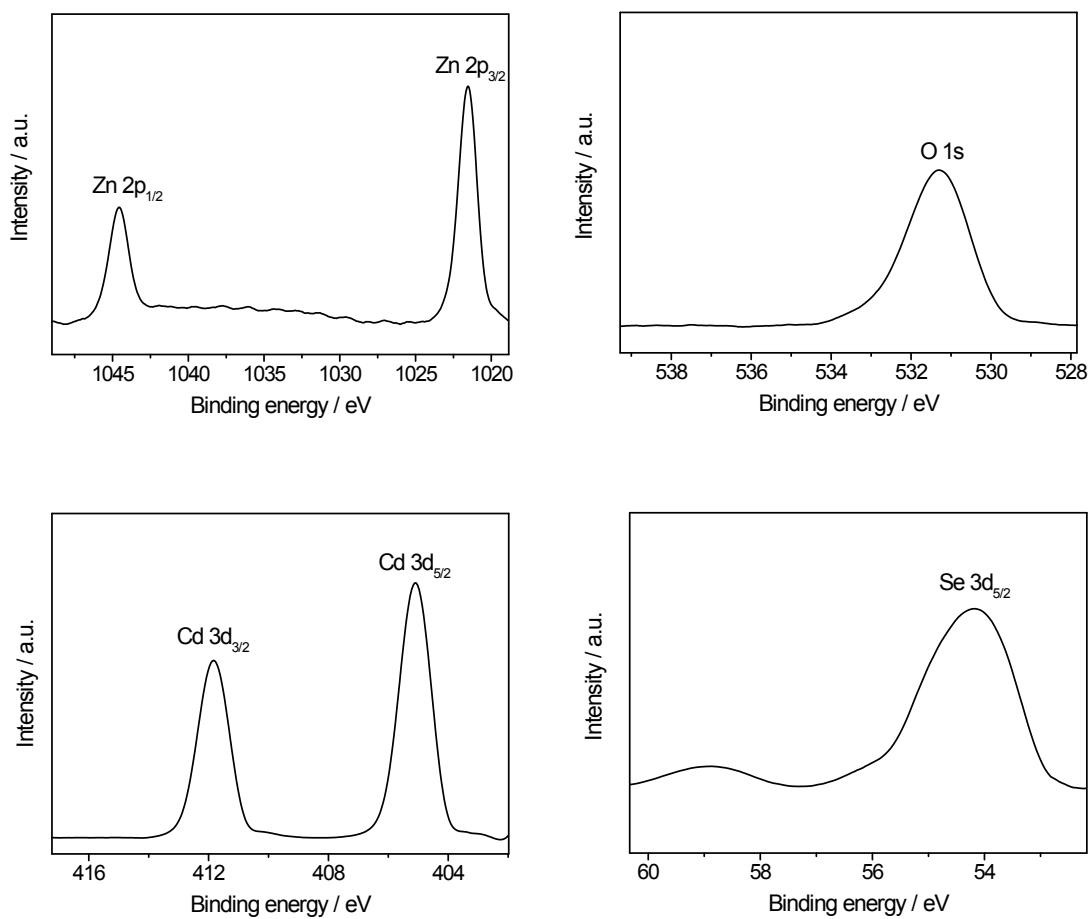


Figure S2. XPS spectra of Zn, O, Cd and Se elements of the ZnO/ZnSe/CdSe/Cu<sub>x</sub>S

Table S1. Photoelectrochemical Performance Using II -VI Group Semiconductor Sensitized ZnO Nanowire/Nanorod Array Photoelectrodes

Electrode Materials	Methods <sup>(a)</sup>	Light Source	Electrolyte	Saturated Photocurrent density (mA/cm <sup>2</sup> )	Maximum IPCE	Ref.
CdSe/ZnO	SILAR	AM 1.5	0.5M Na <sub>2</sub> S	3.5 (0.25V vs Ag/AgCl)	46% at 460 nm	1
CdSe/CdS/ZnO	SILAR-CdS CBD-CdSe	AM 1.5G	1M Na <sub>2</sub> S	9.15 (0V vs SCE)	-	2
IrO <sub>x</sub> ·nH <sub>2</sub> O/CdSe /CdS/ZnO	SILAR-CdS CBD-CdSe	AM 1.5G	0.25M Na <sub>2</sub> S, 0.35M Na <sub>2</sub> SO <sub>3</sub>	13.9 (0.6V vs. RHE)	-	3
ZnO/CdTe/CdS	SILAR-CdS ED-CdTe	AM 1.5G	0.1 M KCl, 0.1 M Na <sub>2</sub> S, 0.3 M S	12.4 (0V vs Ag/AgCl)	-	4
ZnO/CdSe	ED-CdSe	AM 1.5G	0.2 M Na <sub>2</sub> S	14.9 (0.86V vs. RHE)	34% at 410 nm	5
ZnSe/CdS/CdSe/ ZnO	IE-ZnSe CBD-CdS, CdSe	AM 1.5G	0.35 M Na <sub>2</sub> SO <sub>3</sub> , 0.24 M Na <sub>2</sub> S	5.6 (0.25V vs Ag/AgCl)	35% at 380 nm	6
CdSe/CdS/ZnO	SILAR-CdS, CdSe	AM 1.5	0.5 M Na <sub>2</sub> S	14.5 (0.25V vs Ag/AgCl)	-	7
ZnO/ZnSe/CdSe /Cu <sub>x</sub> S	IE-ZnSe, CdSe SILAR-Cu <sub>x</sub> S	AM 1.5G	0.50 M Na <sub>2</sub> S, 0.50 M Na <sub>2</sub> SO <sub>3</sub>	16.7 (0.25V vs Ag/AgCl)	89.5% at 500 nm	This work

(a) SILAR: Successive Ionic Layer Adsorption and Reaction; CBD: Chemical Bath Deposition; ED: Electrochemical Deposition; IE: Ion Exchange;

## References

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